Dimitry Gruznev

List of Publications by Year
in descending order

98	1,012	567281 15	552781 26
papers	citations	h-index	g-index

98	98	98	648
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Self-assembly of C60 layers at Tl/NiSi2 atomic sandwich on Si(111). Surface Science, 2022, 715, 121934.	1.9	1
2	Pb/NiSi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si4.svg"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math> atomic sandwich on Si(111). Surface Science, 2022, 716, 121966.	1.9	4
3	2D system incorporating perforated Mg sheet sandwiched between Pb layer and Si(111). Applied Surface Science, 2022, 589, 152951.	6.1	1
4	Insights Into the Electronic Properties of PbBi Atomic Layers on Ge(111) and Si(111) Surfaces. Frontiers in Materials, 2022, 9, .	2.4	5
5	High quality Mg(0001) films grown on Si(111)<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si3.svg"><mml:mrow><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mo linebreak="goodbreak">Ã—</mml:mo><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt></mml:mrow></mml:math>-B surface at room temperature. Thin Solid Films, 2022, 754, 139317.	1.8	0
6	Single and double In atomic layers grown on top of a single atomic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>NiSi</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math> layer on Si(111). Physical Review B, 2022, 106, .	3.2	4
7	Formation of a double-layer Pb reconstruction on the B-segregated Si(111) surface. Surface Science, 2021, 706, 121784.	1.9	0
8	Electronic and transport properties of Pb-dense reconstructions on Si(100). Surface Science, 2021, 708, 121822.	1.9	5
9	Structural and electronic effects of adsorbed Bi on the metallic atomic chains in Au/Si(111)5ÂÃ—Â2. Applied Surface Science, 2021, 558, 149859.	6.1	5
10	One-dimensional spin-polarized electron channel in the two-dimensional PbBi compound on silicon. Physical Review B, 2021, 104, .	3.2	9
11	Solving a Long-Standing Problem Regarding Atomic Structure of Si(100)2Ã—3-Ag. Journal of Physical Chemistry Letters, 2021, 12, 9584-9587.	4.6	1
12	Metal Sheet of Atomic Thickness Embedded in Silicon. ACS Nano, 2021, 15, 19357-19363.	14.6	6
13	The array of In-Bi heterodimers on the Si(100) surface. Surface Science, 2020, 694, 121557.	1.9	3
14	Fabrication and characterization of a single monolayer NiSi₂ sandwiched between a Tl capping layer and a Si(1â€‰1â€‰1) substrate. 2D Materials, 2020, 7, 025009.	4.4	11
15	Atomic, electronic and transport properties of Inâ€“Au 2D compound on Si(1â€‰0â€‰0). Journal of Physics Condensed Matter, 2020, 32, 135003.	1.8	2
16	C60 capping of metallic 2D Tl-Au compound with preservation of its basic properties at the buried interface. Applied Surface Science, 2020, 501, 144253.	6.1	8
17	Kondo effect at ultimate atomic-scale two-dimensional limit: Au/Si(111) 3Ã—3 reconstruction with embedded Cr atoms. Physical Review B, 2020, 102, .	3.2	3
18	Superconducting proximity effect in a Rashba-type surface state of Pb/Ge(111). Superconductor Science and Technology, 2020, 33, 075007.	3.5	3

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19	Double-atomic-layer Tl-Mg compound on a Si(111) surface with advanced electronic properties. Physical Review B, 2020, 101, .	3.2	5
20	Au-induced reconstructions of the Si(111) surface with ordered and disordered domain walls. Physical Review B, 2020, 101, .	3.2	9
21	Surface reconstructions in Pb/Si(100) system: Composition and atomic arrangement. Surface Science, 2020, 695, 121574.	1.9	8
22	Thallene: graphene-like honeycomb lattice of Tl atoms frozen on single-layer NiSi₂. 2D Materials, 2020, 7, 045026.	4.4	17
23	Superconducting single-atomic-layer Tl-Pb compounds on Ge(111) and Si(111) surfaces. Applied Surface Science, 2019, 479, 679-684.	6.1	10
24	(Tl, Sb) and (Tl, Bi) binary surface reconstructions on Ge(111) substrate. Surface Science, 2018, 669, 183-188.	1.9	1
25	Double-atomic layer of Tl on Si(111): Atomic arrangement and electronic properties. Surface Science, 2018, 668, 17-22.	1.9	9
26	(Tl, Au)/Si(1â€‰1â€‰1)${sqrt7 imes sqrt7}$ 2D compound: an ordered array of identical Au clusters embedded in Tl matrix. Journal of Physics Condensed Matter, 2018, 30, 025002.	1.8	4
27	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. Nanotechnology, 2018, 29, 045602.	2.6	6
28	Thickness Dependence of Surface Structure and Superconductivity in Pb Atomic Layers. Journal of the Physical Society of Japan, 2018, 87, 113601.	1.6	2
29	Two-dimensional metallic (Tl,Au)/Si(100)c(2Ã—2) : A Rashba-type system with C2v symmetry. Physical Review B, 2018, 98, .	3.2	5
30	Electronic properties of the two-dimensional (Tl, Rb)/Si(1â€‰1â€‰1)$oldsymbol{sqrt3 imes sqrt3}$ compound having a honeycomb-like structure. Journal of Physics Condensed Matter, 2018, 30, 415502.	1.8	3
31	From C60 â€œtrilliumonsâ€•to â€œtrilliumenes:â€•Self-assembly of 2D fullerene nanostructures on metal-covered silicon and germanium. Journal of Chemical Physics, 2018, 149, 034702.	3.0	7
32	Two-Dimensional Inâ€“Sb Compound on Silicon as a Quantum Spin Hall Insulator. Nano Letters, 2018, 18, 4338-4345.	9.1	23
33	10.1063/1.5038790.1. , 2018, , .		0
34	Superconductivity in thallium double atomic layer and transition into an insulating phase intermediated by a quantum metal state. 2D Materials, 2017, 4, 025020.	4.4	30
35	Adsorbate-induced modification of electronic band structure of epitaxial Bi(111) films. Applied Surface Science, 2017, 406, 122-127.	6.1	7
36	2D Tlâ€“Pb compounds on Ge(1â€‰1â€‰1) surface: atomic arrangement and electronic band structure. Journal of Physics Condensed Matter, 2017, 29, 035001.	1.8	3

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37	One-atom-layer compounds on silicon and germanium. Japanese Journal of Applied Physics, 2017, 56, 08LA01.	1.5	14
38	Theory versus experiment for a family of single-layer compounds with a similar atomic arrangement: <mml:math		

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55	A Strategy to Create Spin-Split Metallic Bands on Silicon Using a Dense Alloy Layer. Scientific Reports, 2014, 4, 4742.	3.3	65
56	Stepwise self-assembly of C60 mediated by atomic scale moirÃ© magnifiers. Nature Communications, 2013, 4, 1679.	12.8	31
57	Dim C60 fullerenes on Si(111) <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si7.gif" overflow="scroll"><mml:mrow><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mo>Ã—</mml:mo><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mi mathvariant="normal">Ag</mml:mi></mml:mrow></mml:math> surface. Surface Science, 2013, 612, 31-36.	1.9	10
58	Peculiar diffusion of C60 on In-adsorbed Si(111)âˆš3 Ã— âˆš3-Au surface. Surface Science, 2013, 616, 44-50.	1.9	12
59	Large spin splitting of metallic surface-state bands at adsorbate-modified gold/silicon surfaces. Scientific Reports, 2013, 3, 1826.	3.3	51
60	Structural transformations in Pb/Si(111) phases induced by C₆₀ adsorption. Journal of Physics Condensed Matter, 2013, 25, 395006.	1.8	7
61	Modification of the sample holder for a variable temperature scanning tunneling microscope (Omicron). Instruments and Experimental Techniques, 2013, 56, 745-748.	0.5	0
62	ELECTRICAL CONDUCTIVITY STUDY OF Au AND Na COADSORBED Si(111)âˆš3Ã—âˆš3 SURFACE. , 2013, , .		0
63	Surface conduction at phase transitions in (Au,Ag)/Si(111) submonolayer films. Applied Surface Science, 2012, 258, 9636-9641.	6.1	3
64	Modulated<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">C</mml:mi><mml:mrow><mml:mn>60</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>monol on Si(111)<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msqrt><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msqrt></mml:mrow></mml:math> xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo>Ã—</mml:m	3.2	23
65	C60 adsorption onto the one-atomic-layer In films on Si(111) surface. Surface Science, 2011, 605, 1951-1955.	1.9	12
66	Interplay between adsorbed C60 fullerenes and point defects on a Si(111)<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si8.gif" overflow="scroll"><mml:mrow><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mo>Ã—</mml:mo><mml:msqrt><mml:mn>3</mml:mn> reconstructed surface. Surface Science, 2011, 605, 2050-2054.	1.9	6
67	Effect of C60 layer on the growth mode and conductance of Au and Ag films on Si(111)3-Au and Si(111)3-Ag surfaces. Journal of Applied Physics, 2011, 110, 093704.	2.5	10
68	Structural transformations in (Au,In)/Si(111) system and their effect on surface conductivity. Surface Science, 2011, 605, 1420-1425.	1.9	11
69	Broken Even-Odd Symmetry in Self-Selection of Distances between Nanoclusters due to the Presence or Absence of Topological Solitons. Physical Review Letters, 2011, 106, 166101.	7.8	3
70	Effect of Si(100)-c(4 Ã— 12)-Al and Si(111)-(5.55 Ã— 5.55)-Cu reconstructions on the deposition of cobalt onto silicon surface. Technical Physics Letters, 2010, 36, 100-103.	0.7	3
71	Diffusion and clustering of adatoms on discommensurate surface template: Ge atoms on Si(1 1 1)â€œ5 Ã— 5â€•Cu reconstruction. Surface Science, 2010, 604, 666-673.	1.9	5
72	Atomic and electronic structures of Ag/Si(100)-c(6Ã—2) surface: A first-principles study. Surface Science, 2010, 604, 1400-1405.	1.9	5

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73	Effect of Surface Potential Relief on Forming Molecular Arrays: Tryptanthrin Adsorbed on Various Si(111) Reconstructions. Journal of Physical Chemistry C, 2010, 114, 14489-14495.	3.1	10
74	Growth of Au thin film on Cu-modified Si(111) surface. Surface Science, 2009, 603, 3400-3403.	1.9	5
75	Multi-mode growth in Cu/Si(111) system: Magic nanoclustering, layer-by-layer epitaxy and nanowire formation. Surface Science, 2008, 602, 391-398.	1.9	30
76	Self-assembly of conductive Cu nanowires on Si(111)â€˜5 Ã— 5 â€™-Cu surface. Nanotechnology, 2008, 19, 245608.	2.6	7
77	Relative stabilities of adsorbed versus substitutional Al atoms in submonolayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Al</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Si</mml:m <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>4</mml:mn><mml:mo>Ã—</mml:mo><mml:mn>1</mml:mn></mml:mrow></mml:math>to<m Physical Review B, 2008, 78, .	3.2	2
78	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>7</mml:mn><mml:mo>Ã—</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:math>transi in the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mo>â‹…</mml:mo><mml:m Growth of copper nanoislands on the Si(100)-c(4 Ã— 12)-Al surface studied by scanning tunneling microscopy. Technical Physics Letters, 2007, 33, 912-914.	3.2	6
79		0.7	2
80	Growth of In nanocrystallite arrays on the Si(100)-c(4Ã—12)â€“Al surface. Surface Science, 2006, 600, 4986-4991.	1.9	4
81	Reversible phase transitions in the pseudomorphic7Ã—3-hex In layer on Si(111). Physical Review B, 2006, 74, .	3.2	31
82	Si(111)â^Î±â^3Ã—3â^Auphase modified by In adsorption: Stabilization of a homogeneous surface by stress relief. Physical Review B, 2006, 73, .	3.2	44
83	Studying the electric conductivity of the Si(100)c(4Ã—12)-Al surface phase during deposition of indium and aluminum. Technical Physics Letters, 2005, 31, 1068-1070.	0.7	4
84	Surfactant mediated growth of Sb clusters on Si(111) surface. Journal of Crystal Growth, 2004, 269, 235-241.	1.5	12
85	Modification of Sb/Si(001) interface by incorporation of In(4 Ã— 3) surface reconstruction. Applied Surface Science, 2004, 237, 99-104.	6.1	0
86	Atomic structure and formation process of the Si(1 1 1)â€“Sb(â^š7 Ã— â^š7) surface phase. Applied Surface Science, 2003, 212-213, 135-139.	6.1	11
87	Study of Sb adsorption on the Si(0 0 1)â€“In(4 Ã— 3) surface. Applied Surface Science, 2003, 216, 35-40.	6.1	2
88	Surface structure evolution during Sb adsorption on Si(1 1 1)â€“In(4Ã—1) reconstruction. Applied Surface Science, 2002, 190, 134-138.	6.1	18
89	Twinned InSb molecular layer on Si(111) substrate. Surface Science, 2001, 493, 373-380.	1.9	5
90	Sb adsorption on Si(1 1 1)â€“In(4 Ã— 1) surface phase. Applied Surface Science, 2001, 175-176, 187-194.	6.1	5

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91	Growth of high-quality InSb films on Si(111) substrates without buffer layers. Journal of Crystal Growth, 2001, 224, 316-322.	1.5	9
92	Heteroepitaxial growth of high quality InSb films on Si(111) substrates using a two-step growth method. Semiconductor Science and Technology, 2001, 16, 216-221.	2.0	10
93	Structural Transformations During Sb Adsorption on Si(111)â€“In(4Ã—1) Reconstruction. Japanese Journal of Applied Physics, 2001, 40, 4304-4308.	1.5	8
94	Growth temperature effect on the heteroepitaxy of InSb on Si(111). Applied Surface Science, 2000, 159-160, 335-340.	6.1	11
95	The role of the surface phases in surface conductivity. Applied Surface Science, 2000, 162-163, 168-171.	6.1	9
96	Role of In(4Ã—1) superstructure on the heteroepitaxy of InSb on Si(111) substrate. Applied Surface Science, 2000, 162-163, 263-269.	6.1	3
97	Effect of In(4Ã—1) Reconstruction Induced Interface Modification on the Growth Behavior of InSb on Si(111) Substrate. Japanese Journal of Applied Physics, 2000, 39, 3935-3942.	1.5	6
98	Growth-temperature-dependent role of In(4Ã—1) surface phase for the heteroepitaxy of InSb on Si(111). Journal of Applied Physics, 2000, 87, 724-729.	2.5	7